

February 10, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
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Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/736,942 12/16/03 |
| Wenhe Lin et al.

METHODS TO FORM DUAL METAL GATES
BY INCORPORATING METALS AND THEIR
CONDUCTIVE OXIDES

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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P.O. Box 1450, Alexandria, VA 22313-1450, on February , 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 2/12/04

U.S. Patent 6,043,157 to Gardner et al., "Semiconductor Device Having Dual Gate Electrode Material and Process of Fabrication Thereof," discloses a process for forming dual gates where one gate is polysilicon and the other gate is metal.

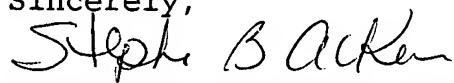
U.S. Patent 6,087,231 to Xiang et al., "Fabrication of Dual Gates of Field Transistors with Prevention of Reaction Between the Gate Electrode and the Gate Dielectric with a High Dielectric Constant," discloses a dummy gate process where amorphous gates doped with different dopants are formed.

U.S. Patent 6,083,836 to Rodder, "Transistors with Substitutionally Formed Gate Structures and Method," teaches a dummy gate process where two gates are formed.

U.S. Patent 5,266,519 to Iwamoto, "Method for Forming a Metal Conductor in Semiconductor Device," teaches oxidation of a metal film to be used as an anti-plating mask.

U.S. Patent Application CS-00-115, Serial #09/981,415, filed on 10/18/01, assigned to the same assignee, now issued as U.S. 6,475,908, describes methods for forming dual-metal gate CMOS transistors.

Sincerely,



Stephen B. Ackerman, Reg. #37761

INFORMATION DISCLOSURE CITATION ON AN APPLICATION <i>FEB 17 2006</i> <i>(Use several sheets if necessary)</i>				Document Number (Opener) CS-00-114BB	Application Number 10/736,942		
				Applicant Wenhe Lin et al.			
				Filing Date 12/16/03	Group Art Unit Group 11 Unit		
U. S. PATENT DOCUMENTS							
EXAMINER'S INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	MUNO DATE X APPROXIMATE	
	60431573	3/28/00	Gardner et al.	438	692	12/18/97	
	6087231	7/11/00	Xiang et al.	438	287	8/5/99	
	60838367	1/4/00	Rodder	438	690	12/18/98	
	5266519	11/30/93	Iwamoto	437	183	11/12/92	
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO	
OTHER DOCUMENTS (Including Author, Title, Date, Page(s), Etc.)							
	U.S. Patent App. CS-00-115, Serial #09/981,415, filed on 10/18/01, same assignee, now issued US 6,475,908, date of Patent 11/5/02, US class 438/659.						
EXAMINER				DATE CONSIDERED			

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.